

Please amend claim 1 as follows:

A2
1. (Amended) A process for treating a substrate with a plasma comprising:
[generating said plasma in the form of plane in a chamber]
generating a plasma in a reaction chamber using a raw material gas introduced
into said reaction chamber through a plurality of inlets provided in a first electrode, wherein said
plurality of inlets are arranged in a first direction; and
moving said substrate adjacent a second electrode for supplying high frequency
power, perpendicularly to said first direction with said substrate being exposed to said plasma.

Please add new claims 18-30 as follows:

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--18. The process of claim 1 wherein ~~the~~ substrate is a magnetic tape or a magnetic disc.

19. The process of claim 1 wherein ~~the~~ plasma is localized in the vicinity of said inlets.

Sub C2
20. A process for treating a substrate with a plasma comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber,
said first electrode having a plurality of gas inlets arranged in a first direction;
introducing a reactive gas through said plurality of gas inlets into said reaction
chamber;
generating a plasma of said reactive gas by applying a voltage between said first
and second electrodes wherein said plasma is localized in the vicinity of said plurality of gas
inlets;
placing a substrate between said first and second electrodes; and
moving said substrate while treating said substrate with said plasma in a second
direction perpendicular to said first direction.

21. The process according to claim 20 wherein a diamond-like carbon film is formed on
said substrate by treating said substrate with the plasma.

22. The process of claim 20 wherein said substrate is a magnetic tape or a magnetic disc.

Sub 7
C3

23. A process for treating a substrate with a plasma comprising the steps of:

- preparing first and second electrodes opposed to each other in a reaction chamber,
- said first electrode having a plurality of gas inlets arranged in a first direction;
- introducing a reactive gas through said plurality of gas inlets into said reaction chamber;
- generating a plasma of said reactive gas by applying a voltage between said first and second electrodes wherein said plasma is localized in the vicinity of said plurality of gas inlets and said first electrode is grounded;
- placing a substrate adjacent to said second electrode; and
- moving said substrate while treating said substrate with said plasma in a second direction perpendicular to said first direction, thereby, forming a diamond-like carbon film on said substrate.

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24. The process according to claim 23 wherein said substrate is a magnetic tape or a magnetic disc.

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25. A process for treating a substrate with a plasma comprising the steps of:

- preparing first and second electrodes opposed to each other in a reaction chamber,
- said first electrode having a plurality of gas inlets;
- introducing a reactive gas through said plurality of gas inlets into said reaction chamber;
- generating a plasma of said reactive gas by applying a voltage between said first and second electrodes wherein said plasma is localized in the vicinity of said plurality of gas inlets;
- placing a substrate between said first and second electrodes; and
- treating said substrate with said plasma,
- wherein a gap between said first and second electrodes is 30 mm or less.

26. The process according to claim 25 wherein said gas is 10 mm or less.

27. The process according to claim 25 wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

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28. A process for treating a substrate with a plasma comprising the steps of:
preparing first and second electrodes opposed to each other in a reaction chamber,
said first electrode having at least one slit-like inlet;
introducing a reactive gas through said slit-like inlet into said reaction chamber;
generating a plasma of said reactive gas by applying a voltage between said first
and second electrodes wherein said plasma is localized in the vicinity of slit-like inlet;
placing a substrate between said first and second electrodes; and
treating said substrate with said plasma,
wherein a gap between said first and second electrodes is 30 mm or less.

A3
amended

29. The process according to claim 28 wherein said gas is 10 mm or less.

30. The process according to claim 28 wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.--

REMARKS

Claims 1 and 18-30 are pending. By this Amendment, claims 2-17 are canceled, claim 1 and the specification are amended, and claims 18-30 are added. Reconsideration in view of the amendments and the following remarks is respectfully requested.

The Office Action objects to the specification for having outdated continuing data and grammatical informalities. Applicants have updated the continuing data and amended the specification in a manner similar to the parent as recommended by the Examiner. Accordingly, withdrawal of the objections to the specification are respectfully requested.

The Office Action rejects claims 1-15 under 35 U.S.C. §112, second paragraph, as indefinite for failing to particularly point out and distinctly claim the subject matter which Applicants regard as the invention. This rejection is respectfully traversed.

Regarding claims 2-15, the rejection is moot. In relation to claim 1, Applicants respectfully submit the amendments to claim 1 obviate the indefiniteness rejection. Accordingly,